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Critical thickness of transition from 2D to 3D growth and peculiarities of quantum dots formation in Ge_xSi_{1-x}/Sn/Si and Ge_{1-y}Sn_y/Si systems

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Highlights

- New approach for modeling growth processes of semiconductor compounds is presented.
- Decrease in 2D-3D transition temperatures for GeSiSn/Si compared to GeSi/Si is explained.
- Dependencies of critical thickness on temperature and composition are explained.
- Islands size decreases with increase in deposition rate and decrease of temperature.
- The simulated data are in a good agreement with experimentally observed results.



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